Unit in mm

## TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

# 2 S C 3 8 6 2

TV TUNER, UHF MIXER APPLICATIONS

VHF~UHF BAND RF AMPLIFIER APPLICATIONS

• Exchange of Emitter for Base in 2SC3120

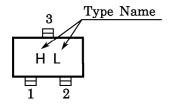
# MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$v_{CBO}$	30	V
Collector-Emitter Voltage	$V_{CEO}$	15	V
Emitter-Base Voltage	$V_{ m EBO}$	3	V
Collector Current	$I_{\mathbf{C}}$	50	mA
Base Current	$I_{\mathrm{B}}$	25	mA
Collector Power Dissipation	$P_{\mathbf{C}}$	150	mW
Junction Temperature	$T_{j}$	125	°C
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~125	°C

# 1. EMITTER 2. BASE 3. COLLECTOR JEDEC — EIAJ — TOSHIBA 2-3F1D

Weight: 0.012g

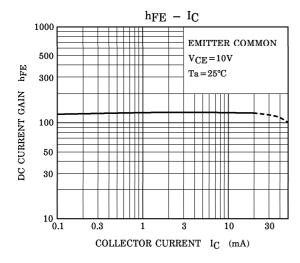
## Marking

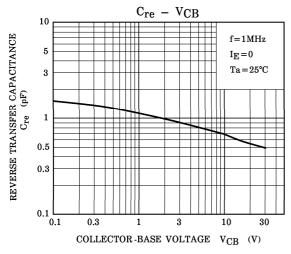


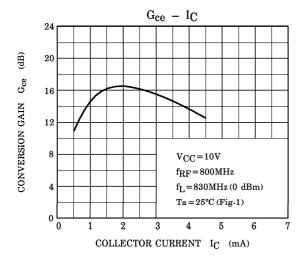
# ELECTRICAL CHARACTERISTICS (Ta = 25°C)

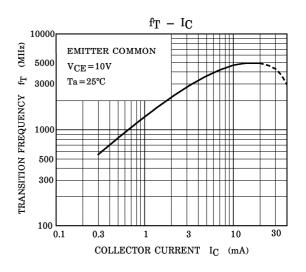
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = 30V, I_{E} = 0$	_	_	0.1	$\mu$ <b>A</b>
Emitter Cut-off Current	$I_{EBO}$	$V_{EB}=2V, I_{C}=0$	_	_	1.0	$\mu$ A
Collector-Emitter Breakdown	V (DD) CDO	$I_{C}=1$ mA, $I_{B}=0$	15		_	V
Voltage	V (BR) CEO					
DC Current Gain	$h_{ extbf{FE}}$	$V_{CE}=10V, I_{C}=5mA$	40	100	200	V
Reverse Transfer Capcitance	$\mathrm{C_{re}}$	$V_{CB} = 10V, I_{E} = 0V, f = 1MHz$	_	0.6	0.9	pF
Transition Frequency	${ m f_T}$	$V_{\text{CE}} = 10V, I_{\text{C}} = 2\text{mA}$	1500	2400	_	MHz

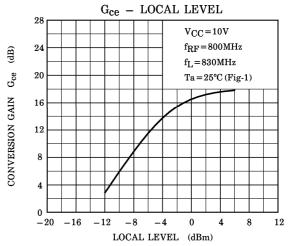
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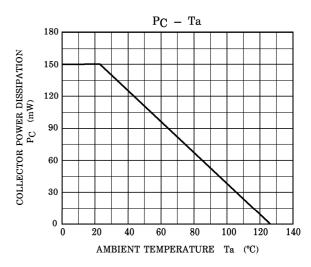








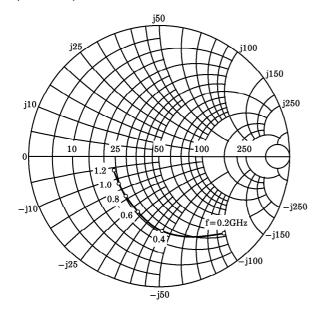


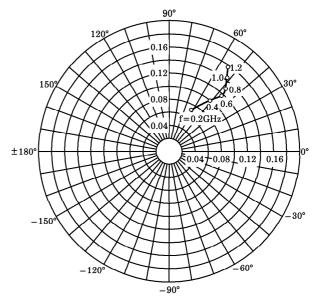


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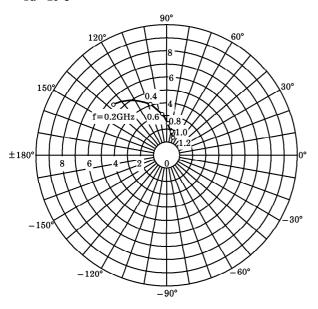
 $\begin{array}{l} S_{11e} \\ V_{CE} = 10V \\ I_{C} = 2mA \\ T_{a} = 25^{\circ}C \\ (UNIT:\Omega) \end{array}$ 

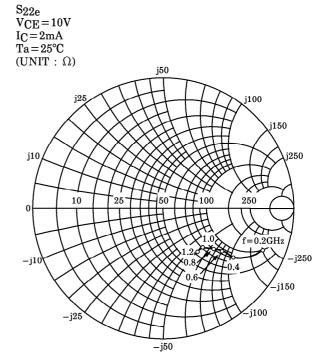






 $\begin{array}{l} \mathrm{S}_{21e} \\ \mathrm{V}_{CE} \!=\! 10\mathrm{V} \\ \mathrm{I}_{C} \!=\! 2\mathrm{mA} \\ \mathrm{Ta} \!=\! 25^{\circ}\!\mathrm{C} \end{array}$ 





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